

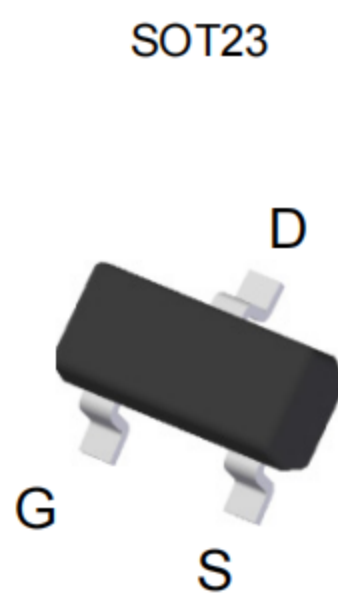
Product Summary

- $V_{DS} = 60V, I_D = 0.3A$
 $R_{DS(ON)} < 2.5 \Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 2.2 \Omega @ V_{GS}=10V$
- ESD Rating : HBM 2000V

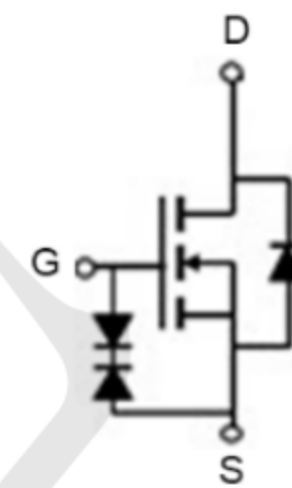
Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays

Package and Pin Configuration



Circuit diagram



Marking: 7002

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150^\circ C$)	I_D	$T_A = 25^\circ C$	0.3
		$T_A = 100^\circ C$	0.19
Drain Current-Pulsed ^(Note 1)	I_{DM}	1.5	A
Maximum Power Dissipation	P_D	0.35	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

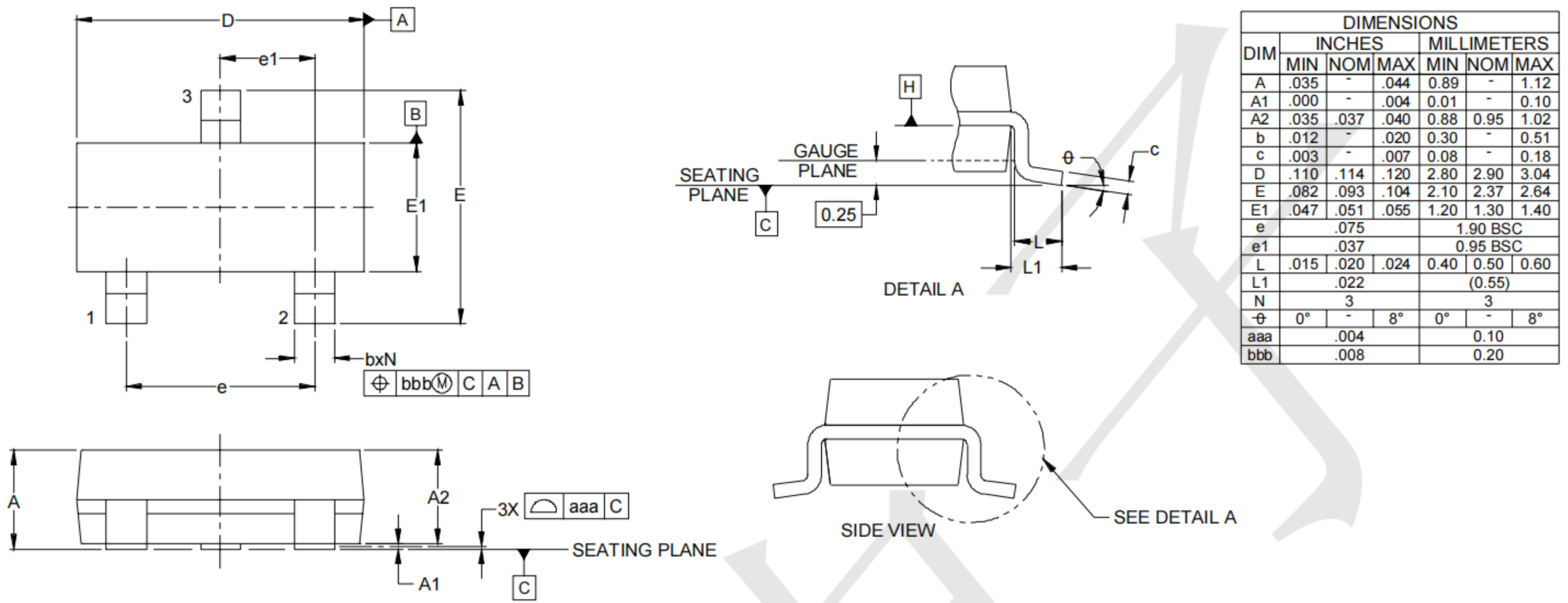
Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	350	$^\circ C/W$
---	-----------------	-----	--------------

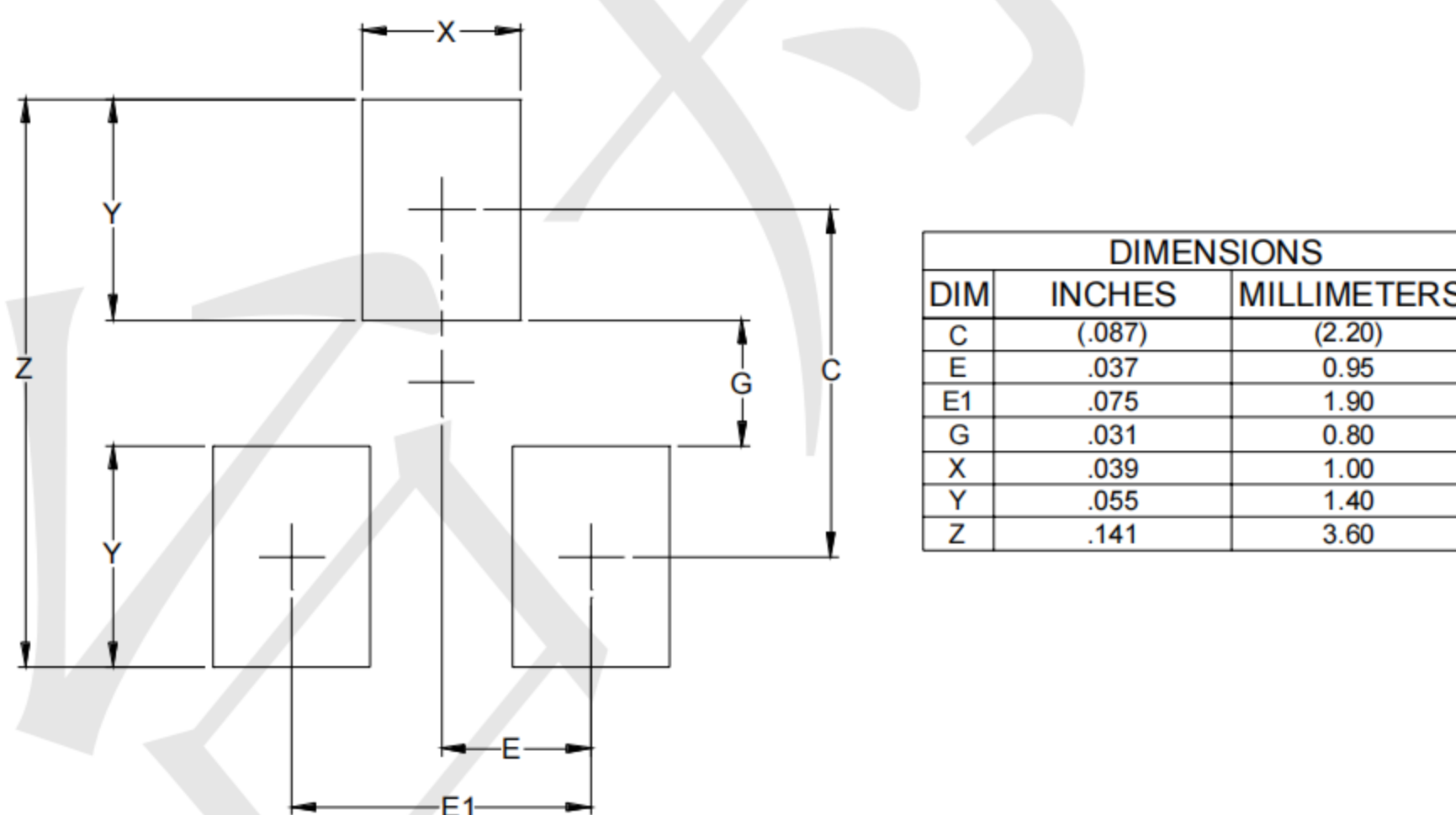
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 1	μA
		$V_{GS}=\pm 20V, V_{DS}=0V$	-		± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.2A$	-	1.9	2.5	Ω
		$V_{GS}=10V, I_D=0.3A$	-	1.8	2.2	Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=0.2A$	0.1	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$		27		PF
Output Capacitance	C_{oss}			18		PF
Reverse Transfer Capacitance	C_{rss}			2		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=0.2A$ $V_{GS}=10V, R_{GEN}=10\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	50	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=0.3A,$ $V_{GS}=4.5V$	-	1.7	3	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=0.2A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	0.3	A

SOT23 - Package Outline Drawing



Suggested Land Pattern



单击下面可查看定价，库存，交付和生命周期等信息

[>>TECH PUBLIC\(台舟\)](#)